NSN 5961-01-245-0815

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-245-0815 **Inclosure Material:** Ceramic **Overall Length:** Between 0.690 inches and 0.770 inches **Overall Height:** 0.350 inches **Overall Width:** Between 0.290 inches and 0.325 inches **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 20.0 gate to source voltage all transistor and 100.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source all transistor **Current Rating Per Characteristic:** 1.00 amperes drain current all transistor and 4.00 amperes off-state current, peak all transistor **Power Rating Per Characteristic:** 1.4 watts total power dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 14 printed circuit **Specification Data:** 81349-mil-s-19500/597 government specification Shelf Life: N/a **Unit Of Measure:** Demilitarization: No